



Product Overview

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MBRS1100: 100 V, 1.0 A Schottky Rectifier

For complete documentation, see the data sheet

Product Description

The Schottky Rectifier employs the Schottky Barrier principle in a large area metal-to-silicon power diode. The Schottky Rectifier's state-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. It is ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes in surface mount applications where compact size and weight are critical to the system.

Features

- Small Compact Surface Mountable Package with J-Bend Leads
- Rectangular Package for Automated Handling
- Highly Stable Oxide Passivated Junction
- High Blocking Voltage - 100 Volts
- 150°C Operating Junction Temperature
- Guardring for Stress Protection

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 95 mg (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

Part Electrical Specifications

Product	Compliance	Status	V _{RRM} Min (V)	V _F Max (V)	I _{RM} Max (uA)	I _{O(rec)} Max (A)	I _{FSM} Max (A)	t _{rr} Max (ns)	C _J Max (pF)	Package Type
MBRS1100T3G	Pb-free Halide free	Active	100	0.75	500	1	50			SMB-2

Package Availability

Type	Pb-free	Standard
SMB-2	✓	✓

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